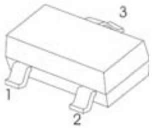
SOT-23 Plastic-Encapsulate MOSFETS

P-Channel 20-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)Typ}$	I_D
-20 V	90mΩ@-4.5V	2.6A
	157mΩ@-2.5V	

SOT-23



1. GATE
2. SOURCE
3. DRAIN

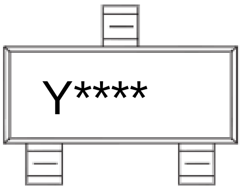
FEATURE

TrenchFET Power MOSFET

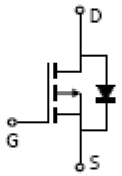
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current (T_J=150℃)	I_D	-2.6	A
Pulsed Drain Current	I_{DM}	-8	
Continuous Source-Drain Diode Current	I_S	-0.72	
Maximum Power Dissipation	P_D	1.3	W
Thermal Resistance from Junction to Ambient(t≤5s)	$R_{\theta JA}$	100	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 ~+150	

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-20			V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.4		-1.1	
Gate-source leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±8V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} =-20V, V_{GS} =0V			-1	μA
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-2.6A		0.090	0.135	Ω
		V_{GS} =-2.5V, I_D =-2.1A		0.157	0.236	
Forward transconductance [a]	g_{fs}	V_{DS} =-5V, I_D =-2.3A		4.0		S
Dynamic[b]						
Input capacitance	C_{iss}	V_{DS} =-10V,V_{GS} =0V,f =1MHz		405		pF
Output capacitance	C_{oss}			75		
Reverse transfer capacitance	C_{rss}			55		
Total gate charge	Q_g	V_{DS} =-10V,V_{GS} =-4.5V,I_D =-3A		5.5	10	nC
		V_{DS} =-10V,V_{GS} =-2.5V,I_D =-3A		3.3	6	
Gate-source charge	Q_{gs}			0.7		
Gate-drain charge	Q_{gd}			1.3		
Gate resistance	R_g	f =1MHz		6.0		Ω
Turn-on delay time	$t_{d(on)}$	V_{DD}=-10V, R_L=10Ω, I_D =-1A, V_{GEN}=-4.5V,Rg=1Ω		11	20	ns
Rise time	t_r			35	60	
Turn-off delay time	$t_{d(off)}$			30	50	
Fall time	t_f			10	20	
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	T_C=25℃			-1.3	A
Pulse diode forward current [a]	I_{SM}				-10	
Body diode voltage	V_{SD}	I_S=-0.7A		-0.8	-1.2	V

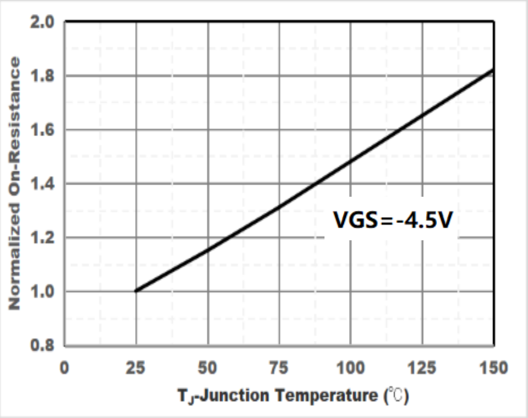
Notes :

a.Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

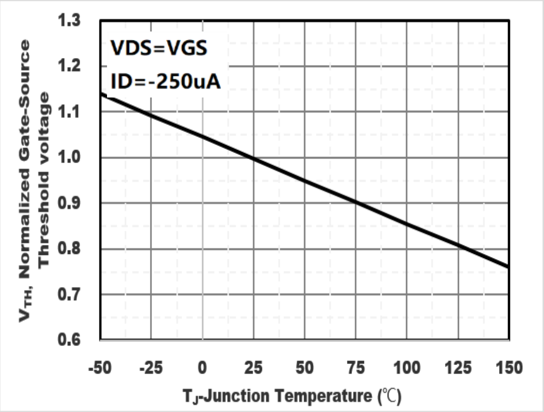
b.Guaranteed by design, not subject to production testing.

Typical Characteristics

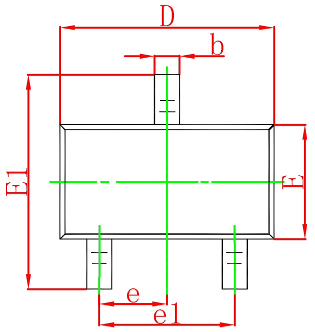
$R_{DS(ON)}$ vs Junction Temperature

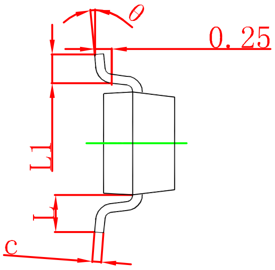


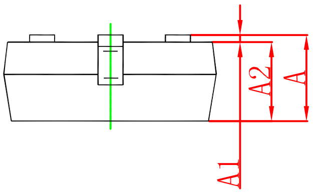
$V_{GS(th)}$ vs Junction Temperature



SOT-23 Package Outline Dimensions

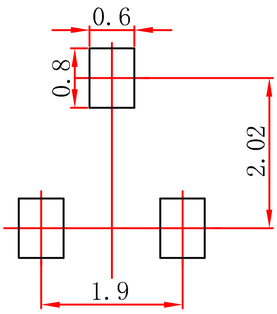






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.